

## EAST Search History

| Ref # | Hits | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|--|---|------------------|---------|------------------|
| L21   | 40   | (soi or besoi or simox or silicon-on-insulator) and (pti or partial\$2 near trench near isolat\$3 or (well or semiconductor) near2 (under or beneath or below or underneath or underlying) near2 (fox or field near oxide)) and (floating near body) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/04/06 17:03 |
| L16   | 8    | "6424011".pn. "5767549".pn.<br>"5026666".pn. "6426558".pn.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/04/06 17:00 |
| L20   | 196  | (soi or besoi or simox or silicon-on-insulator) same (wiring or interconnect\$3 or word near line or wordline or bitline or bit near line) near6 (gate) near6 (source or drain or active or channel)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/04/06 16:27 |
| L19   | 50   | (soi or besoi or simox or silicon-on-insulator) same (local) near2 (interconnect\$3)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/04/06 16:26 |
| L18   | 17   | (soi or besoi or simox or silicon-on-insulator) near10 (local) near2 (interconnect\$3)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/04/06 16:24 |
| L15   | 414  | 257/211,347-351,E27.112.ccls. and (soi or besoi or simox or silicon-on-insulator) near6 (field near oxide or field near oxidation or fox or sti or trench near isolation)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/04/06 16:23 |

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|     |     |  |   |    |    |                  |
|-----|-----|--|---|----|----|------------------|
| L17 | 24  | (US-20040241945-\$ or US-20030002321-\$ or US-20020020878-\$ or US-20040238892-\$ or US-20020112137-\$ or US-20020003241-\$ or US-20030127752-\$ or US-20030102521-\$ or US-20010050397-\$).did. or (US-6590800-\$ or US-6815282-\$ or US-5904512-\$ or US-5756394-\$ or US-6627952-\$ or US-6215155-\$ or US-6424011-\$ or US-5767549-\$ or US-6875663-\$ or US-5116771-\$ or US-6528853-\$ or US-5795800-\$ or US-6483749-\$ or US-5026666-\$ or US-6455894-\$).did. | US-PGPUB;<br>USPAT                                      | OR | ON | 2006/04/06 16:09 |
| L14 | 299 | 257/211,347-351,E27.112.ccls. and (floating adj body) and (field near oxide or field near oxidation or fox or sti or trench near isolation)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/06 15:48 |
| L11 | 77  | 257/211,347-351,E27.112.ccls. and (pti or partial\$2 near2 trench near2 isolati\$3)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/06 14:45 |
| L12 | 3   | ("5116771"   "5726100"   "6018180"). PN.   | US-PGPUB;<br>USPAT;<br>USOCR                            | OR | ON | 2006/04/06 14:39 |
| L7  | 532 | 257/349.ccls.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/06 13:43 |
| L5  | 116 | (soi or silicon-on-insulator or besoi or simox) and (field near oxide or fox or sti or trench near isolation) near4 (under or underneath or beneath or below or underlying or lower) near4 (connection or strap or wire or connecting or doped or well) and gate   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/06 12:59 |
| L4  | 621 | (soi or silicon-on-insulator or besoi or simox) and (floating near body) and (field near oxide or fox or sti or trench near isolation) and gate  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/06 12:18 |

## EAST Search History

|     |     |  |   |    |    |                  |
|-----|-----|--|---|----|----|------------------|
| S69 | 96  | (soi or silicon-on-insulator or besoi or simox) and (pti or partial near trench near isolation)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/06 09:11 |
| S68 | 205 | (soi or box or buried near oxide or tft) and (wiring or interconnection or interconnect or lic) near3 gate near4 (source or drain or impurity or doped or active) and (sram or sdram or dsram) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/05 15:05 |
| S67 | 128 | (tft) and (lic or local near interconnect or local near inter near connect or local near inter-connect)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/05 14:22 |
| S66 | 357 | (soi or box or buried near oxide) and (lic or local near interconnect or local near inter near connect or local near inter-connect) and gate and (source or drain or active) and sram          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2006/04/05 13:51 |

# Inference Search

## EAST Search History

| Ref # | Hits | Search Query  | DBs      | Default Operator | Plurals | Time Stamp       |
|-------|------|---|----------|------------------|---------|------------------|
| L22   | 8    | ((soi or silicon-on-insulator or besoi or simox) and (local near interconnect\$3)).clm.   | US-PGPUB | OR               | ON      | 2006/04/06 17:13 |
| L23   | 0    | ((soi or silicon-on-insulator or besoi or simox) and (cmos or nmos or pmos or mosfet) and (pti or partial\$2 near trench near isolati\$3)).clm.   | US-PGPUB | OR               | ON      | 2006/04/06 17:15 |
| L24   | 10   | ((soi or silicon-on-insulator or besoi or simox) and (cmos or nmos or pmos or mosfet) and (floating near body)).clm.  | US-PGPUB | OR               | ON      | 2006/04/06 17:17 |
| L25   | 1    | ((soi or silicon-on-insulator or besoi or simox) and (well or doped or doping or implant) near3 (under or underneath or below or underlying or beneath or above or upon or overlying) near3 (field near oxide or fox or sti or trench near isolation)).clm. | US-PGPUB | OR               | ON      | 2006/04/06 17:18 |
| L26   | 16   | ((soi or silicon-on-insulator or besoi or simox) and (wiring or interconnect\$3 or lead) near6 gate near6 (drain or source or active)).clm.   | US-PGPUB | OR               | ON      | 2006/04/06 17:19 |
| L28   | 0    | ((soi or silicon-on-insulator or besoi or simox) and (wiring or interconnect\$3 or lead or bitline or bit near line or wordline or word near line) near5 (top or upper) near5 (side or sidewall or edge or wall) near5 gate).clm.                           | US-PGPUB | OR               | ON      | 2006/04/06 17:19 |